

IN THE
UNITED STATES PATENT AND TRADEMARK OFFICE

Inventor(s): David P. Bour et al.

Serial No.:

Examiner:

Filing Date: Herewith

Group Art Unit:

Title: BURIED HETEROSTRUCTURE DEVICE FABRICATED BY SINGLE STEP MOCVD

COMMISSIONER FOR PATENTS
PO Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

This Information Disclosure Statement is submitted:

- ☒ under 37 CFR 1.97(b), or
(Within three months of filing national application; or date of entry of national application; or before mailing date of first office action on the merits; whichever occurs last)
- ☐ under 37 CFR 1.97(c) together with either a:
☐ Statement under 37 CFR 1.97(e), or
☐ a \$180.00 Processing fee under 37 CFR 1.17(p), or
(After the CFR 1.97 (b) time period, but before final action or notice of allowance, whichever occurs first)
- ☐ under 37 CFR 1.97 (d) together with a:
☐ Statement under 37 CFR 1.97(e), and
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Please charge to Deposit Account 50-1078 the sum of \$0.00. At any time during the pendency of this application, please charge any fees required or credit any overpayment to Deposit Account 50-1078 pursuant to 37 CFR 1.25.

☐ Applicant(s) submit herewith Form PTO 1449. References identified with an asterisk (*) were disclosed in Patent Application No. _____ filed _____, now U. S. Patent No. _____, and, as such, copies thereof are not included pursuant to the provisions of 37 CFR 1.98(d).

☐ A concise explanation of the relevance of foreign language patents, foreign language publications and other foreign language information listed on PTO Form 1449, as presently understood by the individuals(s) designated in 37 CFR 1.56 (c) most knowledgeable about the content is given on the attached sheet, or where a foreign language patent is cited in a search report or other action by a foreign patent office in a counterpart foreign application, an English language version of the search report or action which indicates the degree of relevance found by the foreign office is listed on form PTO 1449 and is enclosed herewith.

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I hereby certify that this is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 CFR 1.10 on the date indicated above and is addressed to: Commissioner for Patents, PO Box 1450, Alexandria, VA 22313-1450.

By Linda A. Iimura
Typed Name: Linda A. Iimura

Respectfully submitted,

David P. Bour et al.

By

Ian Hardcastle
Ian Hardcastle

Attorney/Agent for Applicant(s)
Reg. No. 34,075

Date: Feb. 24, 2004

PATENT APPLICATION

FORM PTO-1449

ATTY. DOCKET NO.

SERIAL NO.

10031004-1

**LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT**

APPLICANT

David P. Bour et al.

FILING DATE

GROUP

Herewith

(Use several sheets if necessary)

REFERENCE DESIGNATION**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
	AA					
	AB					
	AC					

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
	AD					
	AE					
	AF					
	AG					
	AH					
	AI					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

	AJ	Bertone, D. et al. "Etching in InP-based MQW Laser Structure in a MOCVD Reactor by Chlorinated Compounds", Journal of Crystal Growth, 195(1998) pp. 624-629.
	AK	Kudo, Koji et al. "Densely Arrayed Eight-Wavelength Semiconductor Lasers Fabricated by Microarray Selective Epitaxy", IEEE Journal of Selected Topics in Quantum Electronics, Vol. 5, NO. 3, May/June 1999, pp. 428-434.
	AL	Tsuchiya, T. et al. "Selective-Area Growth of High-Crystalline-Quality InGaAlAs by Metal-Organic Vapor-Phase Epitaxy", Journal of Crystal Growth, 248(2003), pp. 384-389.
	AM	Sudo, Shinya et al. "Growth Pressure Dependence of Neighboring Mask Interference in Densely Arrayed Narrow-Stripe Selective MOVPE for Integrated Photonic Devices", Journal of Crystal Growth 221 (2000) pp. 189-195.
	AN	
	AO	
	AP	
	AQ	
	AR	

EXAMINER**DATE CONSIDERED**

Rev 5/90 (Form 3.05)